Contents

PREFACE xx

INTRODUCTION xxiii

I.1 THE INFORMATION AGE xxiii

.2 DEMANDS OF THE INFORMATION AGE xxiv

.3 OPTOELECTRONICS: AN ENABLING TECHNOLOGY xxvii

I.4 ELECTRONIC DEVICES: SOME CRACKS IN THE ARMOR xxviii

.5 THE PROMISE OF OPTICAL INFORMATION PROCESSING xxix

I.6 ROLE OF THIS BOOK xxxi

1 MATERIALS FOR OPTOELECTRONICS: STRUCTURAL PROPERTIES

INTRODUCTION 2

.2 STATES OF MATTER: ORDER 2

.3 CRYSTALLINE MATERIALS 4

1.3.1 Periodicity of a crystal 6

1.3.2 Basic lattice types 7

1.3.3 The diamond and zinc blende structures 9

1.3.4 Ferroelectric crystals 10

1.3.5 Notation to denote planes and points in a lattice: Miller indices 12

1.3.6 Artificial structures: Superlattices and quantum wells 16

1.4 INTERFACES 18
1.5 POLYCRYSTALLINE MATERIALS 19
1.6 AMORPHOUS AND GLASSY MATERIALS 20
1.7 LIQUID CRYSTALS 23
1.8 DEFECTS IN MATERIALS 27
.9 SCIENCE AND TECHNOLOGY CHALLENGES 31
1.10 CHAPTER SUMMARY 33
PROBLEMS 34
REFERENCES 39

2 LIGHT PROPAGATION IN MEDIA 41

2.1 INTRODUCTION 42
2.2 MAXWELL EQUATIONS AND THE WAVE EQUATION 42
2.3 POLARIZATION OF LIGHT 48
2.4 FRESNEL FORMULAE: PROPAGATION ACROSS MEDIA 52
2.4.1 Electric vector perpendicular to the plane of incidence 52
2.4.2 Magnetic vector perpendicular to the plane of incidence 54
2.4.3 Polarization effects: Brewster's law 56
2.4.4 Total internal reflection and evanescent fields 58
2.5 WAVE PROPAGATION IN CRYSTALS 62
2.6 LIGHT MODULATION THROUGH POLARIZATION CONTROL 66
2.7 CHAPTER SUMMARY 72
2.8 PROBLEMS 75
2.9 REFERENCES 77

3 LIGHT PROPAGATION IN WAVEGUIDES 78

3.1 INTRODUCTION 79

3.2 WAVEGUIDES: SOME PHYSICAL PROPERTIES 79
3.2.1 Some properties of optical fibers 81

3.3 PLANAR WAVEGUIDES: A GEOMETRICAL OPTICS STUDY 81
3.3.1 Guided modes in a planar waveguide 86

3.4 OPTICAL FIBERS: GEOMETRICAL OPTICS 90

3.5 POLARIZATION CONSTRAINTS IN WAVEGUIDES 92

3.6 GUIDED OPTICAL MODES IN PLANAR WAVEGUIDES 94
3.6.1 Optical confinement factor 99

3.7 OPTICAL FIBERS: WAVE OPTICS 101

3.8 WAVEPACKET PROPAGATION: DISPERSION AND GROUP VELOCITY 107
3.8.1 Motion of a wavepacket 109
3.8.2 Waveguide dispersion 113

3.9 LIGHT COUPLING DEVICES: WAVEGUIDE-TO-WAVEGUIDE COUPLERS 115
3.9.1 Coupled mode theory and the directional coupler 115
3.9.2 Planar-to-planar guide couplers 118
3.9.3 Planar-to-linear guide couplers 120
3.9.4 Waveguide to fiber couplers 121

3.10 BEAM-WAVEGUIDE COUPLERS 122
3.10.1 Transverse coupler 122
3.10.2 The prism coupler 122
3.10.3 The grating coupler 125

3.11 CHAPTER SUMMARY 126

3.12 PROBLEMS 126

3.13 REFERENCES 130

4 ELECTRONIC PROPERTIES OF SEMICONDUCTORS 131

4.1 INTRODUCTION 132

4.2 ELECTRONS IN A PERIODIC POTENTIAL: BLOCH THEOREM 132
4.2.1 From atomic levels to bands 133
4.2.2 The crystal momentum 135

4.3 CONDUCTION AND VALENCE BANDEDGES IN SEMICONDUCTORS 136
4.3.1 Density of states 141

4.4 HOLES IN SEMICONDUCTORS 145

4.5 BANDSTRUCTURES OF SOME SEMICONDUCTORS 146

4.6 MODIFICATION OF BANDSTRUCTURE BY ALLOYING 148

4.7 BANDSTRUCTURE MODIFICATION BY HETEROSTRUCTURES: QUANTUM WELLS 151

INTRINSIC CARRIER CONCENTRATION 155

4.9 DEFECT LEVELS IN SEMICONDUCTORS 158

DOPING IN SEMICONDUCTORS 161
4.10.1 Heavily-doped semiconductors 164
4.10.2 Modulation doping 165

BANDSTRUCTURE OF AMORPHOUS SEMICONDUCTORS 166
4.11.1 Extended and localized states: Mobility edges 167

4.12 CHAPTER SUMMARY 169

4.14 PROBLEMS 173

REFERENCES 176

5 TRANSPORT AND OPTICAL PROPERTIES OF SEMICONDUCTORS 177

5.1 INTRODUCTION 178

5.2 QUANTUM MECHANICS OF SCATTERING PROCESSES 178
5.2.1 The perturbation 180

5.3 TRANSPORT PROPERTIES OF SEMICONDUCTORS: DRIFT IN AN ELECTRIC FIELD 187
5.3.1 Velocity-electric field relations in semiconductors 188
5.3.2 Very high field transport: Breakdown phenomenon 192

5.4 CARRIER TRANSPORT BY DIFFUSION 198
5.4.1 Transport by drift and diffusion 199

5.5 OPTICAL PROPERTIES OF SEMICONDUCTORS 200

5.6 CHARGE INJECTION AND QUASI-FERMI LEVELS 208
5.6.1 Quasi-Fermi levels 209

5.7 CHARGE INJECTION AND RADIATIVE RECOMBINATION 211
5.7.1 Phosphors and fluorescence 216

5.8 CHARGE INJECTION NON-RADIATIVE EFFECTS 218
5.8.1 Defect-related non-radiative processes 219
5.8.2 Auger recombination 220

5.9 THE CONTINUITY EQUATION: DIFFUSION LENGTH 220

MODULATION OF OPTICAL PROPERTIES BY ELECTRIC FIELDS 224
5.10.1 The electro-optic effect 224

5.11 CHAPTER SUMMARY 228

PROBLEMS 232

REFERENCES 235

6 LIGHT DETECTION AND IMAGING 236

6.1 INTRODUCTION 237

6.2 OPTICAL ABSORPTION IN A SEMICONDUCTOR

6.3 PHOTOCURRENT IN A P-N DIODE 244
6.3.1 Application to a solar cell 248

6.4 THE PHOTOCONDUCTIVE DETECTOR 253

6.5 THE P-I-N PHOTODETECTOR 257
6.5.1 Material choice and frequency response of a p-i-n detector 258

6.6 THE AVALANCHE PHOTODETECTOR 261
6.6.1 APD design issues 262

6.7 THE PHOTOTRANSISTOR 266

6.8 METAL-SEMICONDUCTOR DETECTORS

6.9 NOISE AND DETECTION LIMITS 272

6.10 THE RECEIVER AMPLIFIER 278

6.11 THE CHARGED COUPLED DEVICE 281

6.12 ADVANCED DETECTORS 283

6.13 CHAPTER SUMMARY 286

6.14 PROBLEMS 290

6.15 REFERENCES 293

7 THE LIGHT EMITTING DIODE

7.1 INTRODUCTION 295

7.2 MATERIAL SYSTEMS FOR THE LED 295

7.3	OPERATION OF THE LED	298
	7.3.1 Carrier injection and spontaneous emission	300
7.4	EXTERNAL QUANTUM EFFICIENCY	309
7.5	ADVANCED LED STRUCTURES	313
	7.5.1 Heterojunction LED	313
	7.5.2 Edge-emitting LED	314
	7.5.3 Surface-emitting LED	316
7.6	LED PERFORMANCE ISSUES	316
	7.6.1 Light-current characteristics	317
	7.6.2 Spectral purity of LEDs	318
	7.6.3 LED temporal response	320
	7.6.4 Temperature dependence of LED emission	324
7.7	APPLICATION OF LEDS	327
7.8	LED RELIABILITY ISSUES	330
7.9	CHAPTER SUMMARY	
7.10	PROBLEMS	335
7.11	REFERENCES	

8 THE LASER DIODE

8.1	INTRODUCTION	339
8.2	SPONTANEOUS AND STIMULATED EMISSION	
8.3	THE LASER STRUCTURE: THE OPTICAL CAVITY	342
	8.3.1 Optical absorption, loss and gain	344
8.4	THE LASER BELOW AND ABOVE THRESHOLD	350
8.5	THE TIME RESPONSE OF A LASER	356
	8.5.1 Large-signal switching of a laser	359
	8.5.2 Small-signal response of a laser	360

ห้องสมุดกรมวิทยาศาสตร์บริการ

8.6 SEMICONDUCTOR LASER DESIGN: ELECTRONIC STRUCTURE DESIGN 365
8.6.1 Low threshold current 366
8.7 ADVANCED STRUCTURES: TAILORING THE CAVITY 369
8.7.1 Issues in a Fabry-Perot cavity 369
8.7.2 The distributed feedback lasers 373
8.7.3 The surface-emitting laser 376
8.7.4 The DBR laser 379
8.8 TEMPERATURE DEPENDENCE OF LASER OUTPUT 380
8.8.1 Temperature dependence of the threshold current 380
8.8.2 Temperature dependence of the emission frequency 381
8.9 CHAPTER SUMMARY 383
8.10 PROBLEMS 385
8.11 REFERENCES 387

9 MODULATION AND DISPLAY DEVICES 388

9.1 INTRODUCTION 389
9.2 LIQUID CRYSTAL CELLS: THE UNDERLYING PRINCIPLES 390
9.3 CHALLENGES IN SCALING TO A DISPLAY SCREEN 397
9.3.1 The pixel addressing challenge 397
9.3.2 The switch solution 404
9.4 PASSIVE MATRIX LIQUID CRYSTAL DISPLAY 406
9.5 ACTIVE MATRIX LIQUID CRYSTAL DISPLAYS 407
9.5.1 The thin film transistor 408
9.6 CHALLENGES FOR DISPLAY TECHNOLOGY 411
9.6.1 Field emission displays 413
9.7 NEEDS FOR HIGH SPEED LIGHT MODULATION 414
9.7.1 Figures of merit for modulators 416

9.8 ELECTRO-OPTIC MODULATORS

9.9 INTERFEROMETRIC MODULATORS 423
9.9.1 Fabry-Perot modulators 423
9.9.2 Mach-Zender modulators 424

9.10 THE DIRECTIONAL COUPLER 425

9.11 ADVANCED MODULATION AND SWITCHING DEVICES 427
9.11.1 Motivations for quantum well devices 428
9.11.2 Electro-absorption modulators 429

9.12 CHAPTER SUMMARY 431

9.13 PROBLEMS 435

9.14 REFERENCES 437

10 OPTICAL COMMUNICATION SYSTEMS DEVICE NEEDS

10.1 INTRODUCTION

10.2 A CONCEPTUAL PICTURE OF THE OPTICAL COMMUNICATION SYSTEM

10.3 INFORMATION CONTENT AND CHANNEL CAPACITY

10.4 MODULATION AND DETECTION SCHEMES 445
10.4.1 Amplitude modulation 445
10.4.2 Frequency modulation 446
10.4.3 Intensity modulation 448

10.5 SOME PROPERTIES OF OPTICAL FIBERS 448
10.5.1 Fiber losses 449
10.5.2 Multipath dispersion 450
10.5.3 Material dispersion 452
10.5.4 Signal attenuation and detector demands 456
10.5.5 Fiber amplifier 458

SUMMARY OF DEVICE REQUIREMENTS 461

10.7 ADVANCED DEVICES: OPTOELECTRONIC INTEGRATED CIRCUITS (OEICS) 462

CHAPTER SUMMARY 463

PROBLEMS 466

10.10 REFERENCES 467

11 FABRICATION AND PROCESSING OF DEVICES 468

INTRODUCTION 469

SEMICONDUCTORS: BULK CRYSTAL GROWTH 469

EPITAXIAL CRYSTAL GROWTH 471

LITHOGRAPHY 478
11.4.1 Photoresist coating 478
11.4.2 Mask generation and image transfer 481

ETCHING 482
11.5.1 Wet chemical etching 482
11.5.2 Plasma etching 484
11.5.3 Reactive ion beam etching (RIBE) 485
11.5.4 Ion beam milling 485

EPITAXIAL REGROWTH 487

FABRICATION OF OPTICAL FIBERS 489
11.7.1 The preform production and fiber pulling 489

11.8 FIBER COUPLING AND SPLICING 493

CHAPTER SUMMARY 496

PROBLEMS 496

11.11 REFERENCES 499

A LIST OF SYMBOLS 500

IMPORTANT PROPERTIES OF SEMICONDUCTORS 506

C DENSITY OF STATES 511

C.1 INTRODUCTION 511

C.2 THE ELECTRON WAVEFUNCTION AND THE DENSITY OF STATES 511
C.2.1 Density of states for a 3-dimensional system 513
C.2.2 Density of states in sub-3-dimensional systems 515

THE P-N DIODE: A SUMMARY 518

D.1 INTRODUCTION 518

D.2 THE P-N JUNCTION 518
D.2.1 The unbiased p-n junction 519
D.2.2 P-N junction under bias 524
D.2.3 Charge injection and current flow 525
D.2.4 The real diode: Effects of defects 528

INDEX 530